
Contents

Preface	ix
Chapter 1. Introduction and Reminders	1
1.1. A brief history of microelectronics	1
1.1.1. Electricity: Ampère, Coulomb, Faraday, Gauss, Henry, Kirchhoff, Maxwell, Ohm	1
1.1.2. Vacuum tube	1
1.1.3. Early applications	2
1.1.4. Computers (transistors–trans-resistors + integrated circuits (IC))	3
1.1.5. Analysis and theory	5
1.1.6. Transistor	5
1.1.7. Integrated circuits	6
1.1.8. Field-effect transistor	7
1.1.9. Digital integrated circuits	8
1.1.10. Volatile memory (read and write)	9
1.1.11. MOS	9
1.1.12. CCD (MOS): charge-coupled device (“multi-gate” MOS)	10
1.1.13. Manufacturing technique	10
1.1.14. CAD: computer-aided design	12
1.2. Technological computer-aided design	15
1.3. Manufacturing	15
1.3.1. Diffusion processes	17
1.3.2. Diffusion modeling	20
1.4. PN junction (an overview)	21
1.4.1. The non-polarized PN junction	23
1.4.2. Directly polarized PN junction	25

1.4.3. The reverse polarized junction	25
1.4.4. Polarization of the junction	27
1.5. The transistor effect	32
1.5.1. Controlling the current gain	33
1.6. MOSFET (Metal Oxide Semiconductor Field-Effect Transistor)	34
1.6.1. Base structure	34
1.6.2. Functioning principle	35
1.6.3. Electric model for the MOS capacitor and C(V) curve	36
Chapter 2. Modeling of Diffusion Processes	39
2.1. Introduction	39
2.2. Phenomenological equations of diffusion	41
2.2.1. Fick's first law	44
2.2.2. Generalized flux	46
2.2.3. Fick's second law	47
2.2.4. Codiffusion(s)	48
2.3. Calculation of flux and the internal electric field effect	49
2.4. Influence of different vacancies on the diffusion coefficient	52
2.5. Calculation of the electric field in the case of arsenic	53
2.6. An example: modeling the diffusion of dopants in polysilicon grains and joints	55
2.7. Microscopic processes	65
2.7.1. Brownian motion	66
2.7.2. Diffusion mechanisms and correlation effects	69
2.8. Phenomenological theory of diffusion	75
2.9. Review of the thermodynamics of irreversible processes	75
2.10. Conclusion	79
2.11. Appendix 1	80
2.11.1. Matlab global code	85
2.11.2. Conclusion to Appendix 1	87
2.12. Appendix 2	87
2.12.1. Introduction	87
2.12.2. Construction of a dynamic simulator	88
2.12.3. Modeling the rebound of a particle on a wall	92
2.12.4. Ideal gas in a box	93
Chapter 3. Electrical Functioning of Devices	99
3.1. Introduction	99
3.1.1. Near-future directions	99
3.1.2. Scientific motivation	101
3.1.3. Current	103
3.1.4. Possible approach	103

3.2. Current state diagram	104
3.2.1. Drift diffusion model	104
3.2.2. Rapid devices for radiofrequency or microwave systems	120
3.2.3. DGMOSFET	126
3.3. Wigner function	133
3.3.1. Wigner–Boltzmann equation	137
3.3.2. Schrödinger–Poisson model	138
3.3.3. Numerical results	143
3.3.4. Short-channel effects	144
3.4. Electromagnetism; MOS: Maxwell equations	147
3.4.1. Introduction	147
3.4.2. Maxwell equations	148
3.4.3. Overview of the FDTD method	150
3.4.4. Perfect electric conductor (PEC)	154
3.4.5. Perfect magnetic conductor (PMC)	154
3.4.6. Absorbing condition	155
3.4.7. Modeling localized linear equations	158
3.4.8. Interconnection simulations	162
3.5. Substrate in tridimensional circuits at micro- and nanoelectronic levels	170
3.5.1. Introduction	170
3.5.2. Mathematical tools	171
3.5.3. Analogy with transmission lines for multilayer substrates	175
3.5.4. Green/TLM results	177
3.5.5. Heat equation	180
3.6. Conclusion	185
3.7. Appendix	185
3.7.1. P–N junction: working; recap	185
3.7.2. Scharfetter–Gummel algorithm	186
3.8. Constants and data	190
3.9. Finite elements, under MATLAB (NPN)	228
3.9.1. Structure definition	228
3.9.2. Assembly	230
3.9.3. Solving: pros and cons of the finite element method	230
Chapter 4. Background Noise in Micro- and Nanoelectronics	233
4.1. Introduction	233
4.2. Fluctuations and noise	234
4.2.1. Recap on Dirac distribution	234
4.2.2. Random functions, correlation and spectral densities of fluctuations	235
4.3. Noise calculation using the Langevin method	237

4.3.1. Principle of the Langevin method	237
4.3.2. Example: generation–recombination noise	238
4.3.3. Quantities associated with noise in electricity	239
4.3.4. Example application: thermal noise of a resistor	240
4.3.5. Forms of Langevin equations	241
4.3.6. Example: electron injection in the p area of a PN junction	242
4.4. Noise calculation using the impedance field method	243
4.4.1. Principle of the method	243
4.4.2. Impedance fields	243
4.4.3. Calculation of the impedance field	245
4.4.4. Example application: noise in the ohmic space charge regime (simple injection)	246
4.5. Noise calculation using the transfer impedance method principle: formulation	248
4.5.1. Principle	249
4.5.2. One-dimensional structures	250
4.6. Substrate noise: towards 3D	253
4.7. Appendix	254
4.7.1. Calculation: δn , δp , $\delta \Phi$	254
4.8. Conclusion	261
Bibliography	263
Index	269